RF MOS FIELD EFFECT TRANSISTOR

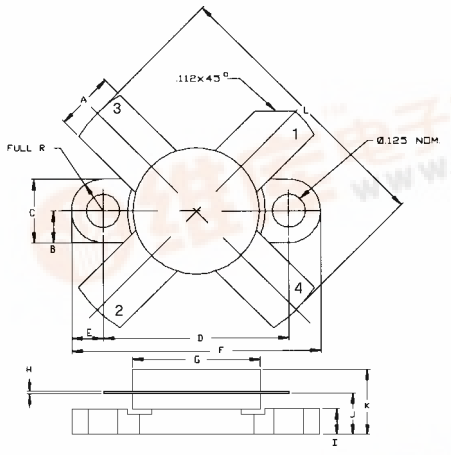
DESCRIPTION:

The **SRF4245** is Designed for class AB HF/VHF Aplications up to 200 MH_Z

FEATURES:

- P_G = 8 dB at 150 MHz
- ***Omnigold***™ Metallization System

PACKAGE STYLE .500 4L FLG



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5,59	.230/5,84
B	.125/3,18	
C	.245/6,22	.255/6,48
D	.720/18,28	.730/18,54
E	.125/3,18	
F	.970/24,64	.980/24,89
G	.495/12,57	.505/12,83
H	.003/0,08	.007/0,18
I	.090/2,29	.110/2,79
J	.160/4,06	.175/4,45
K		.280/7,11
L		1.050/26,67

MAXIMUM RATINGS

I_D	13.9 A
$V_{(BR)DS}$	125 V
V_{DGR}	125 V
V_{GS}	± 30 V
P_{DISS}	215 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.70 (Typ) °C/W

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$V_{(BR)\ DSS}$	V_{GS} = 0 V	I_D = 100 mA		125			V
I_{DSS}	V_{DS} = 50 V	V_{GS} = 0 V				5	mA
I_{GSS}	V_{GS} = 20 V	V_{DS} = 0 V				1	µA
$V_{FEDS(on)}$	V_{GS} = 10 V	I_D = 10 A				5	V
G_{FS}	V_{DS} = 10 V	I_D = 5.0 A		4			mhos
C_{ISS} C_{OSS} C_{RSS}	V_{DS} = 50 V	V_{GS} = 0 V	F = 1.0 MHz			500 250 50	pF
POUT P_G	V_{DS} = 50 V	I_{DQ} = 250 mA	F = 150 MH_Z	150 8			W dB